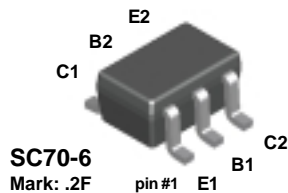


## FFB2907A

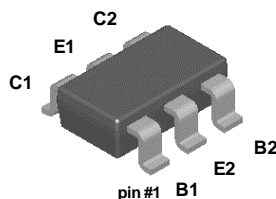


SC70-6

Mark: .2F

NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.

## FMB2907A

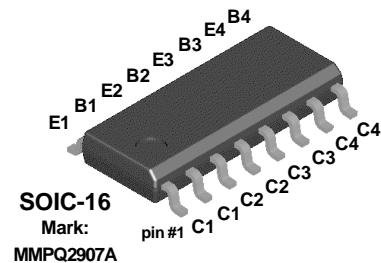


SuperSOT™-6

Mark: .2F

Dot denotes pin #1

## MMPQ2907A



SOIC-16

Mark:  
MMPQ2907A

## PNP Multi-Chip General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current - Continuous	600	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2907A	FMB2907A	MMPQ2907A	
$P_D$	Total Device Dissipation	300	700	1,000	mW
	Derate above $25^\circ\text{C}$	2.4	5.6	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180		$^\circ\text{C}/\text{W}$
	Effective 4 Die			125	$^\circ\text{C}/\text{W}$
	Each Die			240	$^\circ\text{C}/\text{W}$

# PNP Multi-Chip General Purpose Amplifier

(continued)

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	5.0			V
$I_B$	Base Cutoff Current	$V_{CB} = 30\text{ V}, V_{EB} = 0.5\text{ V}$			50	nA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30\text{ V}, V_{BE} = 0.5\text{ V}$			50	nA
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 50\text{ V}, I_E = 0$ $V_{CB} = 50\text{ V}, I_E = 0, T_A = 125^\circ\text{C}$			0.02 20	$\mu\text{A}$ $\mu\text{A}$

## ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}^*$	75 100 100 100 50		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{ mA}, I_B = 15\text{ mA}^*$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.3 2.6	V V

## SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		250		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0,$ $f = 100\text{ kHz}$		6.0		pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 2.0\text{ V}, I_C = 0,$ $f = 100\text{ kHz}$		12		pF

## SWITCHING CHARACTERISTICS

$t_{on}$	Turn-on Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$ $I_{B1} = 15\text{ mA}$		30		ns
$t_d$	Delay Time			8.0		ns
$t_r$	Rise Time			20		ns
$t_{off}$	Turn-off Time	$V_{CC} = 6.0\text{ V}, I_C = 150\text{ mA}$ $I_{B1} = I_{B2} = 15\text{ mA}$		80		ns
$t_s$	Storage Time			60		ns
$t_f$	Fall Time			20		ns

\*Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

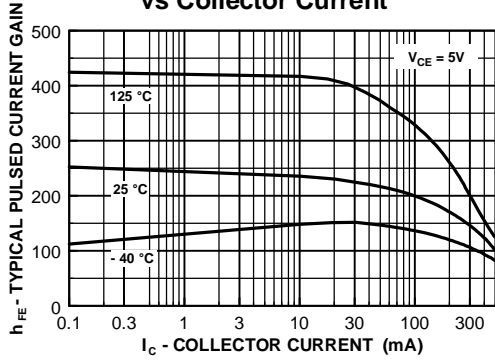
## Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)

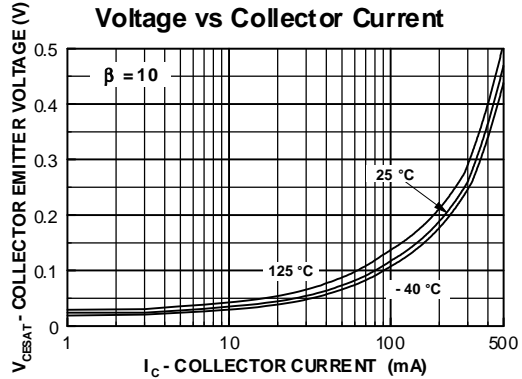
FFB2907A / FMB2907A / MMPQ2907A

Typical Characteristics

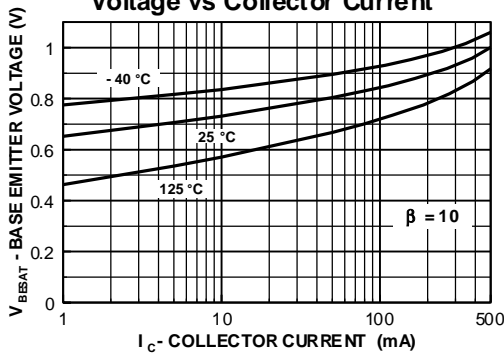
Typical Pulsed Current Gain vs Collector Current



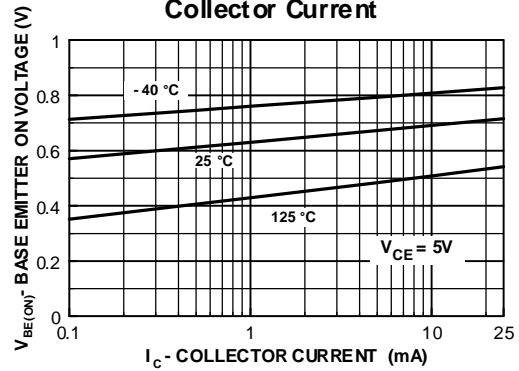
Collector-Emitter Saturation Voltage vs Collector Current



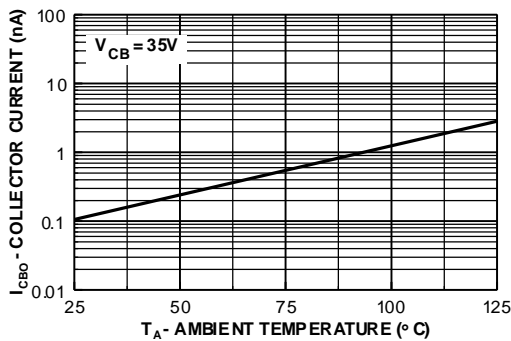
Base-Emitter Saturation Voltage vs Collector Current



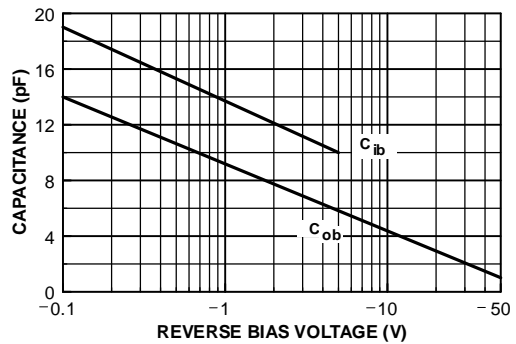
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Input and Output Capacitance vs Reverse Bias Voltage



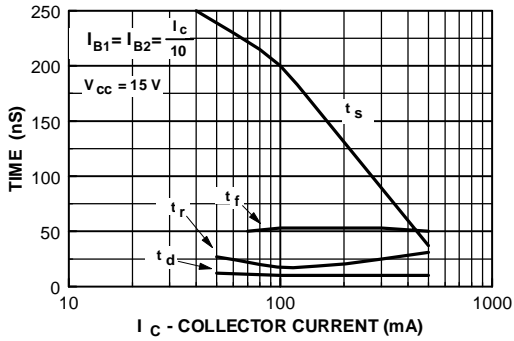
# PNP Multi-Chip General Purpose Amplifier

(continued)

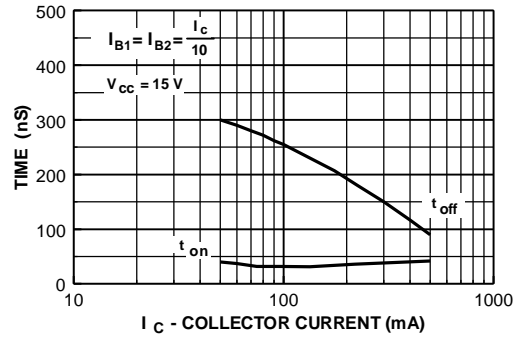
FFB2907A / FMB2907A / MMPQ2907A

## Typical Characteristics (continued)

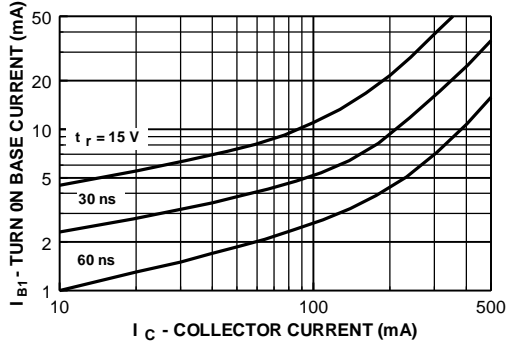
### Switching Times vs Collector Current



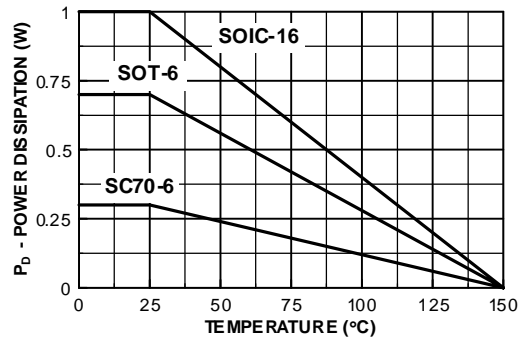
### Turn On and Turn Off Times vs Collector Current



### Rise Time vs Collector and Turn On Base Currents



### Power Dissipation vs Ambient Temperature

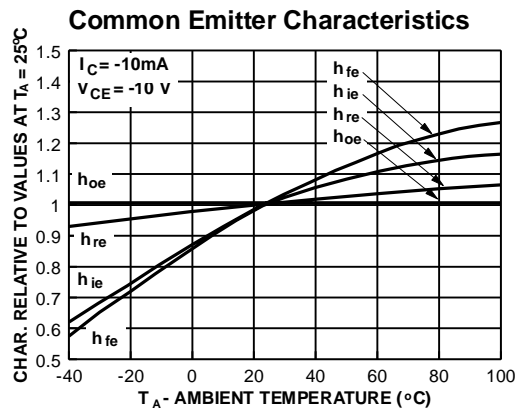
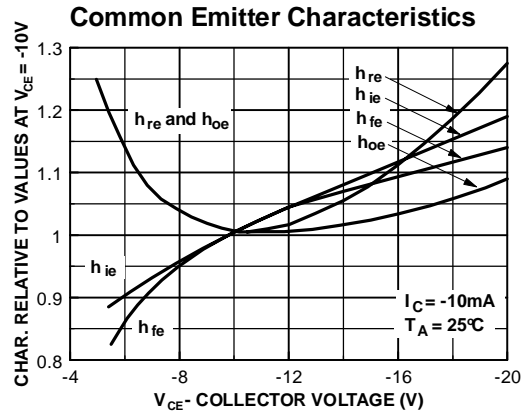
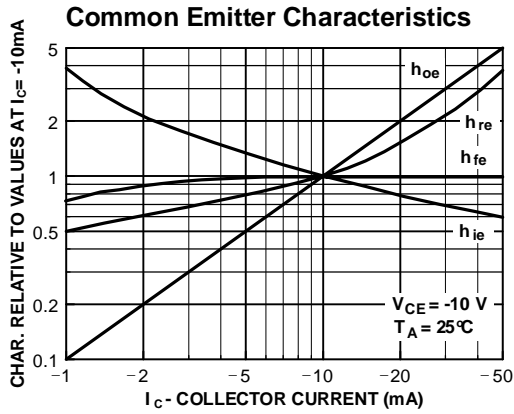


# PNP Multi-Chip General Purpose Amplifier

(continued)

FFB2907A / FMB2907A / MMPQ2907A

## Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

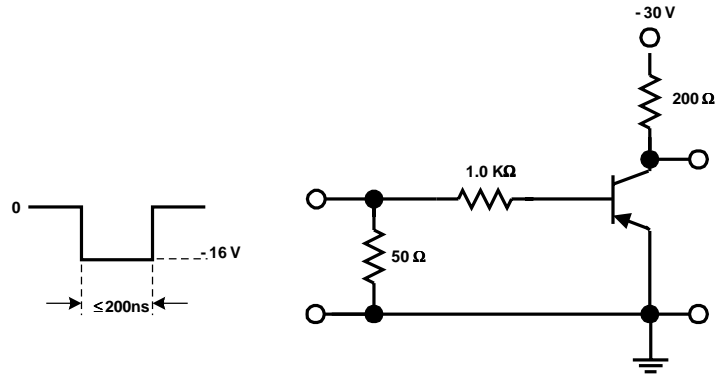


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

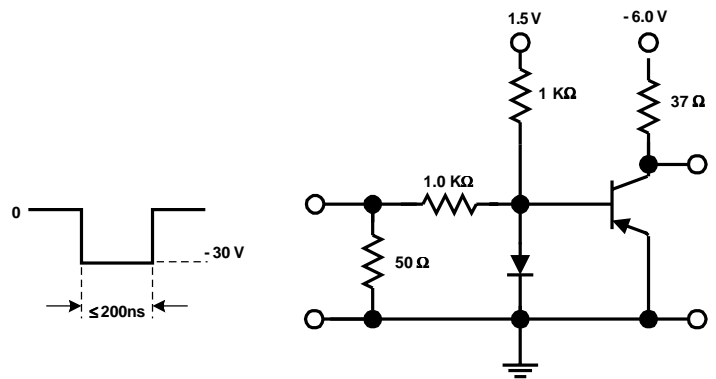


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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DOME™	ISOPLANAR™	Quiet Series™	
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